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Complementary silicon power transistors.

The 2N3773 powerbase[™] power transistors designed for high power audio, disk head positioners and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers. DC-DC converters or inverters.

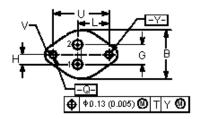
Features:

- Pb-free packages.
- High safe operating area (100% tested) 150W at 100V.
- Completely characterized for linear operation.
- High DC current gain and low saturation voltage.
 h_{FE} = 15 (minimum) at 8.0A, 4.0V.

 $V_{CE (sat)}$ = 1.4V (maximum) at I_C = 8.0A, I_B = 0.8A.

• For low distortion complementary designs.

	(TO-3)
<u>↓</u> ੈ_E	A → C C → C C → C → C C → C → C → C → C →



Style 1:

- Pin 1. Base
 - 2. Emitter Collector (Case)

Dimensions	NA 1	NA	
Dimensions	Minimum	Maximum	
А	1.550 (39.37) Reference		
В	-	1.050 (26.67)	
С	0.250 (6.35)	0.335 (8.51)	
D	0.038 (0.97)	0.043 (1.09)	
E	0.055 (1.40)	0.070 (1.77)	
G	0.430 (10.92) BSC		
Н	0.215 (5.46) BSC		
к	0.440 (11.18)	0.480 (12.19)	
L	0.665 (16.89) BSC		
N	-	0.830 (21.08)	
Q	0.151 (3.84)	0.165 (4.19)	
U	1.187 (30.15) BSC		
V	0.131 (3.33)	0.188 (4.77)	

Dimensions : Inches (Millimetres)

16A Complementary Power Transistors 140V, 150W



(TO-3) Case 1-07

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Maximum Ratings (Note 1)

	Rating	Symbol	2N3772	Unit	
Collector-Emitter Voltage		V _{CEO}	140		
Collector-Emitter Voltage		V _{CEX}	400		
Collector-Base Voltage		V _{CBO}	- 160	V dc	
Emitter-Base Voltage	9	V _{EBO}	7		
Collector Current	- Continuous - Peak (Note 2)	Ι _C	16 30	A do	
Base Current	- Continuous - Peak (Note 2)	۱ _B	4 15	A dc	
Total Device Dissipa Derate above 25°C	tion at T _A = 25°C	P _D	150 0.855	W W/°C	
Operating and Stora	ge Junction Temperature Range	T _{J,} T _{stg}	-65 to +200	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Indicates JEDEC registered data.

2. Pulse test: pulse width = 5μ s, duty cycle $\leq 10\%$.

Thermal Characteristics

Characteristics	Symbol	Maximum	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	1.17	°C/W

Electrical Characteristics (T_c = 25°C unless otherwise noted)

Characteristic	Symbol	Minimum	Maximum	Unit	
Off Characteristics (Note 3)				1	
Collector-Emitter Breakdown Voltage (Note 4) ($I_c = 0.2 \text{ A dc}, I_B = 0$)	V _{EO (sus)}	140	-		
Collector-Emitter Sustaining Voltage (Note 4) ($I_C = 0.1A dc, V_{EB (off)} = 1.5 Vdc, R_{BE} = 100\Omega$)	V _{CEX(sus)}	160	-	V dc	
Collector-Emitter Sustaining Voltage ($I_C = 0.2A \text{ dc}, R_{BE} = 100\Omega$)	V _{CER(sus)}	150	-		
Collector Cut off Current (Note 4) (V_{CE} = 120V dc, I_B = 0)	I _{CEO}	-	10		
Collector Cut off Current (Note 4) (V_{CE} = 140V dc, $V_{EB (off)}$ = 1.5V dc) (V_{CE} = 140V dc, $V_{EB (off)}$ = 1.5V dc, T_{C} = 150°C)	I _{CEX}	-	2 10	mA dc	

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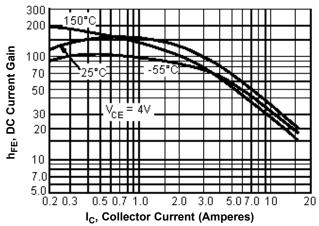
Electrical Characteristics (T_c = 25°C unless otherwise noted)

Characteristic	Symbol	Minimum	Maximum	Unit
Collector Cut off Current (V _{CB} = 140V dc, I _E = 0)	I _{CBO}	-	2	and all a
Emitter Cut off Current (Note 4) (V_{BE} = 7Vdc, I_{C} = 0)	I _{EBO}	-	5	mA dc
On Characteristic (Note 3)				
DC Current Gain ($I_C = 8A dc, V_{CE} = 4V dc$) (Note 4) ($I_C = 16A dc, V_{CE} = 4V dc$)	h _{FE}	15 5	60 -	-
Collector-Emitter Saturation Voltage ($I_C = 8A dc$, $I_B = 800 mA dc$) (Note 4) ($I_C = 16A dc$, $I_B = 3.2A dc$)	V _{CE (sat)}	-	1.4 4	V dc
Base-Emitter On Voltage (Note 4) (I _C = 8A dc, V _{CE} = 4V dc)	V _{BE (on)}	-	2.2	
Dynamic Characteristics				
Magnitude of Common-Emitter Small-Signal, Short-Circuit, Forward Current Transfer Ratio (I _C = 1A, f = 50kHz)	h _{fe}	4	-	-
Small-Signal Current Gain (Note 4) (I _C = 1A dc, V _{CE} = 4V dc, f = 1 kHz)	h _{fe}	40	-	-
Second Breakdown Characteristics	·			
Second Breakdown Collector Current with Base Forward Biased t = 1s (non-repetitive), V_{CF} = 100V	I _{S/b}	1.5	-	A dc

3. Pulse Test: Pulse Width = $300\mu s$, Duty Cycle $\leq 2\%$.

4. Indicates JEDEC Registered Data.

DC Current Gain

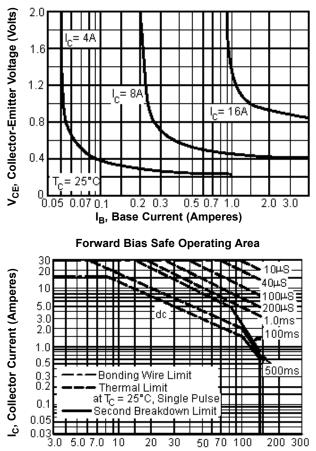


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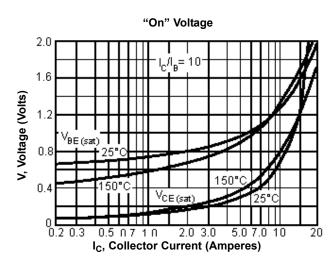


Collector Saturation Region

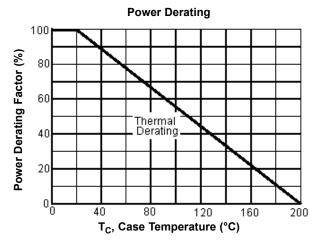
V _{CE} , Collector-Emitter	· Voltage	(Volts)
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Part Number Table

Description	Part Number
Transistor, NPN, TO-3	2N3773



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate. The data is based on $T_{J (PK)} = 200^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J (PK)} < 200^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



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